



2N3906

SMALL SIGNAL PNP TRANSISTOR

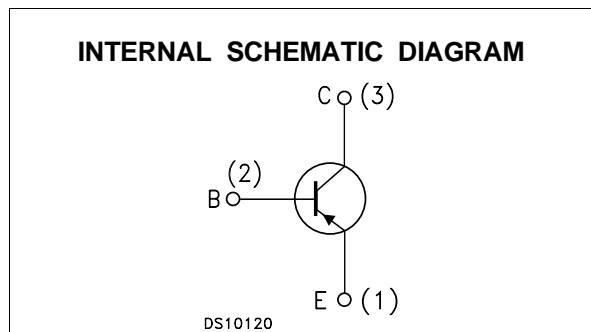
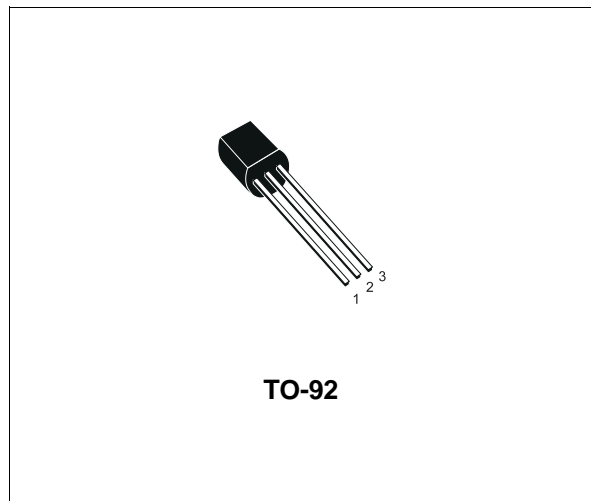
PRELIMINARY DATA

Type	Marking
2N3906	2N3906

- SILICON EPITAXIAL PLANAR PNP TRANSISTOR
- TO-92 PACKAGE SUITABLE FOR THROUGH-HOLE PCB ASSEMBLY
- THE PNP COMPLEMENTARY TYPE IS 2N3904

APPLICATIONS

- WELL SUITABLE FOR TV AND HOME APPLIANCE EQUIPMENT
- SMALL LOAD SWITCH TRANSISTOR WITH HIGH GAIN AND LOW SATURATION VOLTAGE



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	-60	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	-40	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	-6	V
I_C	Collector Current	-200	mA
P_{tot}	Total Dissipation at $T_C = 25\text{ }^\circ\text{C}$	625	mW
T_{stg}	Storage Temperature	-65 to 150	$^\circ\text{C}$
T_j	Max. Operating Junction Temperature	150	$^\circ\text{C}$

THERMAL DATA

R _{thj-amb} •	Thermal Resistance Junction-Ambient	Max	200	°C/W
R _{thj-Case} •	Thermal Resistance Junction-Case	Max	83.3	°C/W

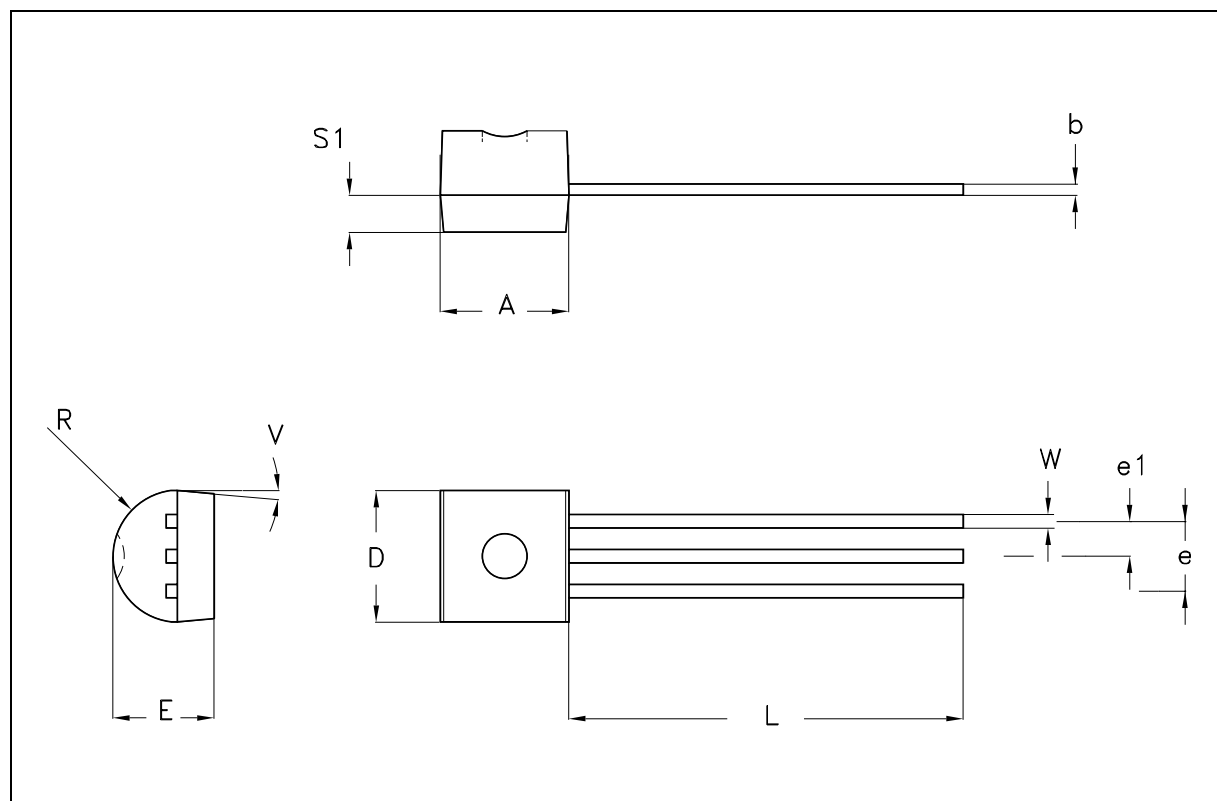
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEX}	Collector Cut-off Current (V _{BE} = 3 V)	V _{CE} = -30 V			-50	nA
I _{BEX}	Base Cut-off Current (V _{BE} = 3 V)	V _{CE} = -30 V			-50	nA
V _{(BR)CEO*}	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = -1 mA	-40			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	I _C = -10 μA	-60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = -10 μA	-6			V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = -10 mA I _B = -1 mA I _C = -50 mA I _B = -5 mA			-0.25 -0.4	V V
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C = -10 mA I _B = -1 mA I _C = -50 mA I _B = -5 mA	-0.65		-0.85 -0.95	V V
h _{FE*}	DC Current Gain	I _C = -0.1 mA V _{CE} = -1 V I _C = -1 mA V _{CE} = -1 V I _C = -10 mA V _{CE} = -1 V I _C = -50 mA V _{CE} = -1 V I _C = -100 mA V _{CE} = -1 V	60 80 100 60 30		300	
f _T	Transition Frequency	I _C = -10mA V _{CE} = -20 V f = 100 MHz	250			MHz
NF	Noise Figure	V _{CE} = -5 V I _C = -0.1 mA f = 10 Hz to 15.7 KHz R _G = 1 KΩ		4		dB
C _{CBO}	Collector-Base Capacitance	I _E = 0 V _{CB} = -5 V f = 100 KHz		6		pF
C _{EBO}	Emitter-Base Capacitance	I _C = 0 V _{EB} = -0.5 V f = 100 KHz		25		pF
t _d	Delay Time	I _C = -10 mA I _B = -1 mA			35	ns
t _r	Rise Time	V _{CC} = -3V			35	ns
t _s	Storage Time	I _C = -10 mA I _{B1} = -I _{B2} = -1 mA			225	ns
t _f	Fall Time	V _{CC} = -3V			72	ns

* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %

TO-92 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.32		4.95	0.170		0.195
b	0.36		0.51	0.014		0.020
D	4.45		4.95	0.175		0.194
E	3.30		3.94	0.130		0.155
e	2.41		2.67	0.095		0.105
e1	1.14		1.40	0.045		0.055
L	12.70		15.49	0.500		0.609
R	2.16		2.41	0.085		0.094
S1	1.14		1.52	0.045		0.059
W	0.41		0.56	0.016		0.022
V	4 degree		6 degree	4 degree		6 degree



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